



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

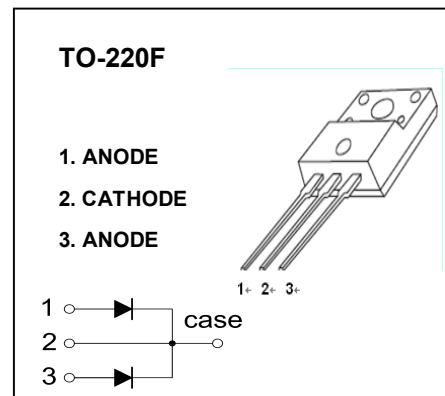
TO-220F Plastic-Encapsulate Diodes

SBL1030, 35, 40, 45, 50FCT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value					Unit
		SBL10 30FCT	SBL10 35FCT	SBL10 40FCT	SBL10 45FCT	SBL10 50FCT	
V_{RRM}	Peak repetitive reverse voltage						
V_{RWM}	Working peak reverse voltage	30	35	40	45	50	V
V_R	DC blocking voltage						
$V_{R(RMS)}$	RMS reverse voltage	21	24.5	28	31.5	35	V
I_o	Average rectified output current			10			A
I_{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave			175			A
P_D	Power dissipation			2			W
$R_{\Theta JA}$	Thermal resistance from junction to ambient			50			$^\circ\text{C}/\text{W}$
T_j	Junction temperature			125			$^\circ\text{C}$
T_{stg}	Storage temperature			-55~+150			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Device	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V _(BR)	SBL1030FCT	I _R =0.5mA	30			V
		SBL1035FCT		35			
		SBL1040FCT		40			
		SBL1045FCT		45			
		SBL1050FCT		50			
Reverse current	I _R	SBL1030FCT	V _R =30V			0.5	mA
		SBL1035FCT	V _R =35V				
		SBL1040FCT	V _R =40V				
		SBL1045FCT	V _R =45V				
		SBL1050FCT	V _R =50V				
Forward voltage	V _F	SBL1030FCT-1045FCT	I _F =5A			0.55	V
		SBL1050FCT				0.7	
Typical total capacitance	C _{tot}	SBL1030FCT-1050FCT	V _R =4V,f=1MHz		450		pF